AMENDMENT TO THE CLAIMS

Please amend the claims as follows:

1. (Canceled)

2. (Currently Amended) A method for manufacturing a semiconductor device comprising the step of:

forming an insulating film comprising silicon nitride over a semiconductor by sputtering in an atmosphere ~~consisting essentially of~~ comprising nitrogen at 75 volume % or more.

3. (Previously Presented) A method according to claim 2 wherein the sputtering is performed by an RF sputtering method.

4. (Previously Presented) A method according to claim 2 wherein the semiconductor device is incorporated into an active matrix display device.

5. (Currently Amended) A method for manufacturing a semiconductor device comprising the step of:

forming an insulating film comprising silicon nitride over a semiconductor by sputtering in an atmosphere ~~consisting of~~ comprising nitrogen at 75 volume % or more and argon at 25 volume % or less.

6. (Previously Presented) A method according to claim 5 wherein the sputtering is performed by an RF sputtering method.

7. (Previously Presented) A method according to claim 5 wherein the semiconductor device is incorporated into an active matrix display device.

8. (Currently Amended) A method according to claim 5 wherein the atmosphere ~~contains nitrogen at 75 volume% or more and argon at 25 volume% or less~~ further comprises halogen at 0.2 to 20 volume %

9. (Currently Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming an insulating film comprising silicon nitride over a semiconductor by sputtering in an atmosphere ~~consisting essentially of~~ comprising nitrogen at 75 volume % or more; and

forming an electrode comprising aluminum over the insulating film.

10. (Previously Presented) A method according to claim 9 wherein the sputtering is performed by an RF sputtering method.

11. (Previously Presented) A method according to claim 9 wherein the semiconductor device is incorporated into an active matrix display device.

12. (Currently Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming an insulating film comprising silicon nitride over a semiconductor by sputtering in an atmosphere ~~consisting of~~ comprising nitrogen at 75 volume % or more and argon at 25 volume % or less; and

forming an electrode comprising aluminum over the insulating film.

13. (Previously Presented) A method according to claim 12 wherein the sputtering is performed by an RF sputtering method.

14. (Previously Presented) A method according to claim 12 wherein the semiconductor device is incorporated into an active matrix display device.

15. (Currently Amended) A method according to claim 12 wherein the atmosphere ~~contains nitrogen at 75 volume% or more and argon at 25 volume% or less~~ further comprises halogen at 0.2 to 20 volume %.

16. (Currently Amended) A method for manufacturing a semiconductor device comprising the step of:

forming a transistor; and

forming an insulating film comprising silicon nitride over the transistor by sputtering in an atmosphere ~~consisting essentially of~~ comprising nitrogen at 75 volume % or more.

17. (Previously Presented) A method according to claim 16 wherein the sputtering is performed by an RF sputtering method.

18. (Previously Presented) A method according to claim 16 wherein the semiconductor device is incorporated into an active matrix display device.

19. (Currently Amended) A method for manufacturing a semiconductor device comprising the step of:

forming a transistor; and

forming an insulating film comprising silicon nitride over the transistor by sputtering in an atmosphere ~~consisting of~~ comprising nitrogen at 75 volume % or more and argon at 25 volume % or less.

20. (Previously Presented) A method according to claim 19 wherein the sputtering is performed by an RF sputtering method.

21. (Previously Presented) A method according to claim 19 wherein the semiconductor device is incorporated into an active matrix display device.

22. (Currently Amended) A method according to claim 19 wherein the atmosphere ~~contains nitrogen at 75 volume% or more and argon at 25 volume% or less~~ further comprises halogen at 0.2 to 20 volume %.